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# GaAlAs-IR-Lumineszenzdiode in SMT-Gehäuse

## GaAlAs Infrared Emitter in SMT Package

SFH 421

SFH 426



SFH 421



SFH 426

### Wesentliche Merkmale

- GaAlAs-LED mit sehr hohem Wirkungsgrad
- Gute Linearität ( $I_e = f[I_F]$ ) bei hohen Strömen
- Gleichstrom- (mit Modulation) oder Impulsbetrieb möglich
- Hohe Zuverlässigkeit
- Hohe Impulsbelastbarkeit
- Oberflächenmontage geeignet
- Gegurtet lieferbar
- SFH 421 Gehäusegleich mit SFH 320
- SFH 426 Gehäusegleich mit SFH 325
- SFH 426: Nur für IR-Reflow-Lötung geeignet.

### Anwendungen

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb, Lochstreifenleser
- Industrielektronik
- „Messen/Steuern/Regeln“
- Automobiltechnik
- Sensorik
- Alarm- und Sicherungssysteme
- IR-Freiraumübertragung

### Features

- Very highly efficient GaAlAs-LED
- Good Linearity ( $I_e = f[I_F]$ ) at high currents
- DC (with modulation) or pulsed operations are possible
- High reliability
- High pulse handling capability
- Suitable for surface mounting (SMT)
- Available on tape and reel
- SFH 421 same package as SFH 320
- SFH 426 same package as SFH 325
- SFH 426: Suitable only for IR-reflow soldering.

### Applications

- Miniature photointerrupters
- Industrial electronics
- For drive and control circuits
- Automotive technology
- Sensor technology
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 421	Q62702-P1055	Kathodenkennzeichnung: abgesetzte Ecke cathode marking: bevelled edge TOPLED®
SFH 426	Q62702-P0331	SIDELED

**Grenzwerte ( $T_A = 25 \text{ }^\circ\text{C}$ )****Maximum Ratings**

<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>	<b>Einheit Unit</b>
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	$^\circ\text{C}$
Sperrspannung Reverse voltage	$V_R$	5	V
Durchlaßstrom Forward current	$I_F$	100	mA
Stoßstrom, $\tau = 10 \mu\text{s}, D = 0$ Surge current	$I_{FSM}$	2.5	A
Verlustleistung Power dissipation	$P_{tot}$	180	mW
Wärmewiderstand Sperrsicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm <sup>2</sup> Thermal resistance junction - ambient mounted on PC-board (FR4), pads size 16 mm <sup>2</sup> each Wärmewiderstand Sperrsicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	$R_{thJA}$ $R_{thJS}$	450 $\approx 200$	K/W K/W

Kennwerte ( $T_A = 25^\circ\text{C}$ )

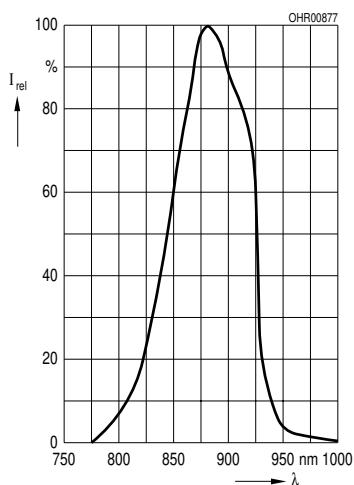
Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$\lambda_{\text{peak}}$	880	nm
Spektrale Bandbreite bei 50% von $I_{\text{max}}$ Spectral bandwidth at 50% of $I_{\text{max}}$ $I_F = 100 \text{ mA}$	$\Delta\lambda$	80	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 60$	Grad deg.
Aktive Chipfläche Active chip area	$A$	0.09	$\text{mm}^2$
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3 $\times$ 0.3	mm
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 100 \text{ mA}, R_L = 50 \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 100 \text{ mA}, R_L = 50 \Omega$	$t_r, t_f$	0.5	$\mu\text{s}$
Kapazität, Capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	$C_o$	15	pF
Durchlaßspannung, Forward voltage $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	$V_F$ $V_F$	1.5 ( $\leq 1.8$ ) 3.0 ( $\leq 3.8$ )	V V
Sperrstrom, Reverse current $V_R = 5 \text{ V}$	$I_R$	0.01 ( $\leq 1$ )	$\mu\text{A}$
Gesamtstrahlungsfluß, Total radiant flux $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$\Phi_e$	23	mW
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ , $I_F = 100 \text{ mA}$ Temperature coefficient of $I_e$ or $\Phi_e$ , $I_F = 100 \text{ mA}$	$TC_I$	- 0.5	%/K
Temperaturkoeffizient von $V_F$ , $I_F = 100 \text{ mA}$ Temperature coefficient of $V_F$ , $I_F = 100 \text{ mA}$	$TC_V$	- 2	mV/K
Temperaturkoeffizient von $\lambda$ , $I_F = 100 \text{ mA}$ Temperature coefficient of $\lambda$ , $I_F = 100 \text{ mA}$	$TC_\lambda$	+ 0.25	nm/K

**Strahlstärke  $I_e$  in Achsrichtung**gemessen bei einem Raumwinkel  $\Omega = 0.01 \text{ sr}$ **Radiant Intensity  $I_e$  in Axial Direction**at a solid angle of  $\Omega = 0.01 \text{ sr}$ 

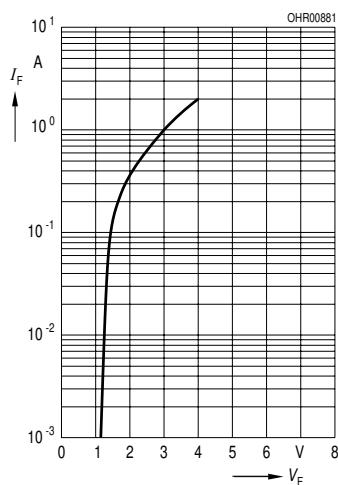
Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$I_e$	> 4	mW/sr
Strahlstärke Radiant intensity $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	$I_{e \text{ typ}}$	48	mW/sr

**Relative Spectral Emission**  
 $I_{\text{rel}} = f(\lambda)$

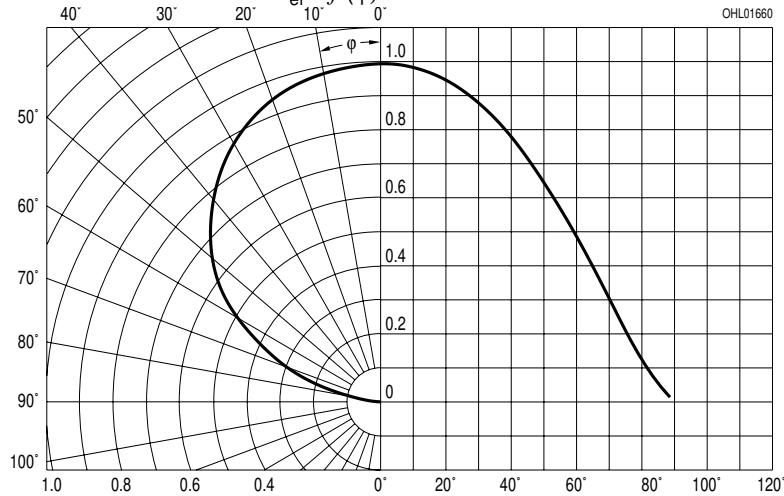


**Forward Current**

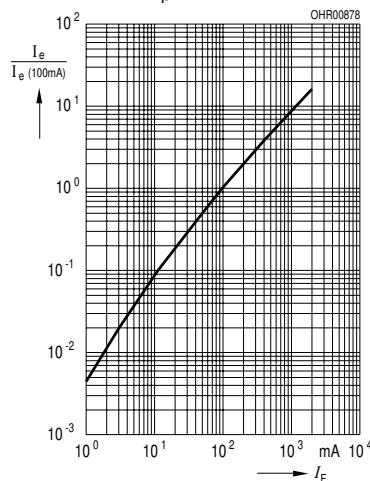
$I_F = f(V_F)$  single pulse,  $t_p = 20 \mu\text{s}$



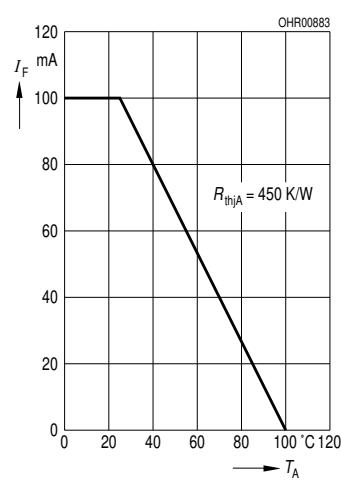
**Radiation Characteristics**  $S_{\text{el}} = f(\phi)$



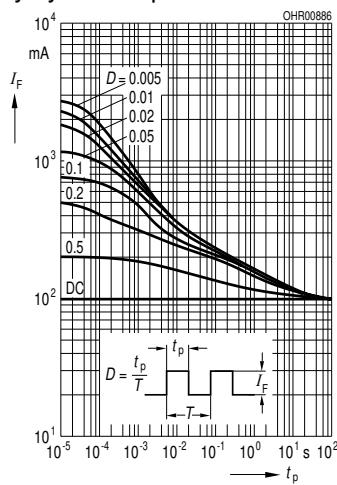
**Radiant Intensity**  $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$   
Single pulse,  $t_p = 20 \mu\text{s}$



**Max. Permissible Forward Current**  
 $I_F = f(T_A)$

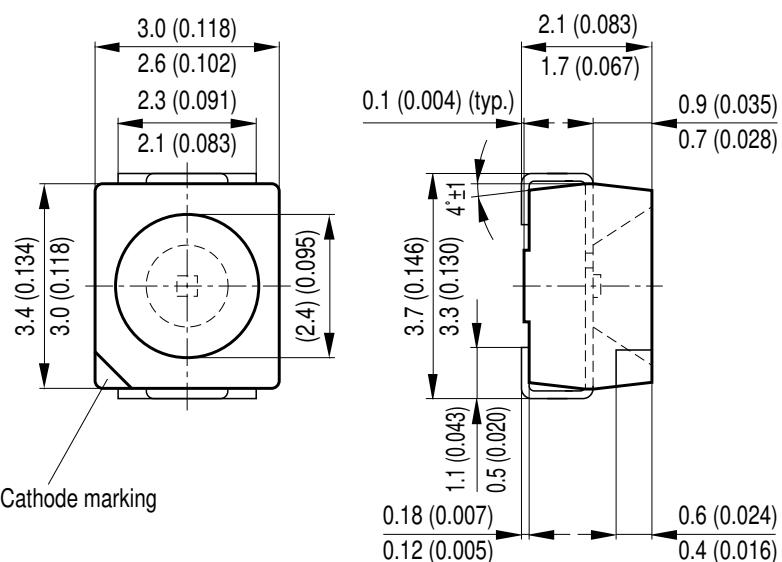


**Permissible Pulse Handling Capability**  $I_F = f(t_p)$ ,  $T_A = 25^\circ\text{C}$   
duty cycle  $D = \text{parameter}$



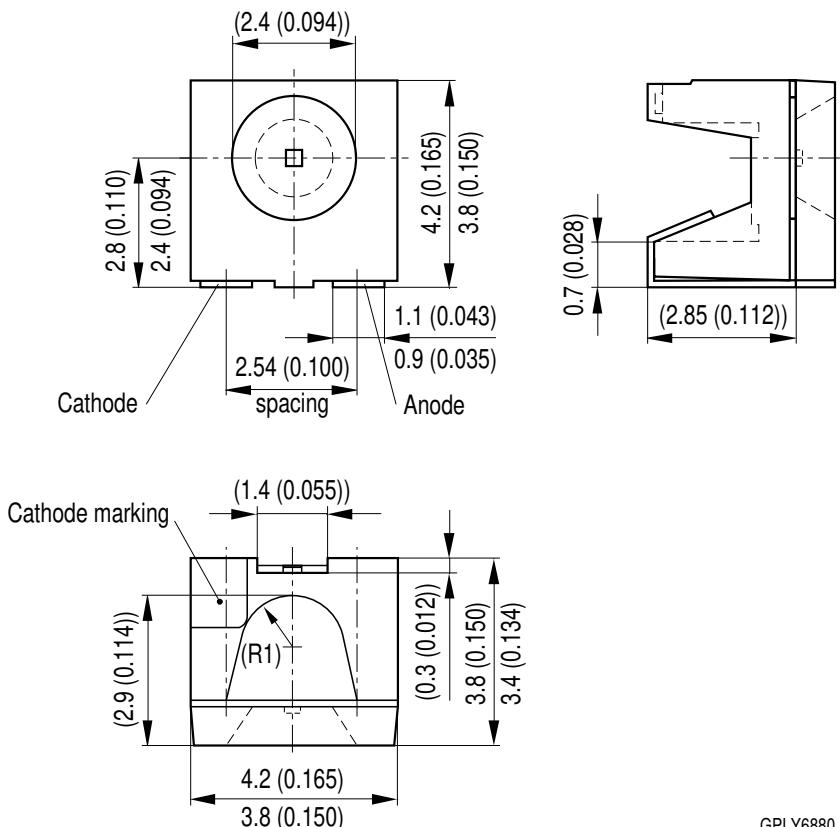
**Maßzeichnung  
Package Outlines**

SFH 421



GPLY6724

SFH 426



GPLY6880

Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

**Löthinweise**  
**Soldering Conditions**

<b>Bauform</b> <b>Types</b>	<b>Tauch-, Schwall- und Schlepplötzung</b> <b>Dip, Wave and Drag Soldering</b>			<b>Reflowlötzung</b> <b>Reflow Soldering</b>	
	<b>Lötbad-temperatur</b> <b>Temperature of the Soldering Bath</b>	<b>Maximal zulässige Lötzeit</b> <b>Max. Perm. Soldering Time</b>	<b>Abstand Lötstelle – Gehäuse</b> <b>Distance between Solder Joint and Case</b>	<b>Lötzonen-temperatur</b> <b>Temperature of Soldering Zone</b>	<b>Maximale Durchlaufzeit</b> <b>Max. Transit Time</b>
TOPLED®	260 °C	8 s	–	245 °C	10 s
SIDELED	260 °C	8 s	–	245 °C	10 s

Zusätzliche Informationen über allgemeine Lötbedingungen erhalten Sie auf Anfrage.

For additional information on general soldering conditions please contact us.

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**Attention please!**

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**Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

**Components used in life-support devices or systems must be expressly authorized for such purpose!** Critical components<sup>1</sup>, may only be used in life-support devices or systems<sup>2</sup> with the express written approval of OSRAM OS.

<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

<sup>2</sup> Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.